

RTD120D

Silicon-Based Thermopile Detector 120 Dual

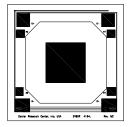
The RTD120D is a two-channel silicon-based thermopile detector in a TO-5 package. The device offers a low-cost solution with high output and fast response, with a time constant of 25ms with Nitrogen encapsulation gas.

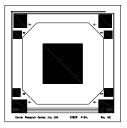
Image Diagram





Detector Circuit Overlay





Applications

- Gas analysis
- Fire suppression
- Non-contact temperature sensors
- Horizon sensors
- Capnography

Features

- A two-channel silicon-based thermopile detector in a TO-5 package
- Five pin, 9.22mm TO-5 package
- Each small active area size is 1.2 × 1.2 mm
- Delivers a time constant of 25ms with Nitrogen encapsulation gas
- Very low Temperature Coefficient of Responsivity of -0.04%/°C
- Very short thermal shock response to ambient temperature change
- Internal 5% NTC chip thermistor provides ambient package temperature measurement
- Internal aperture precisely defines active area for applications with FOV and/or spot size requirements

Benefits

Low cost with high sensitivity and high output

1. Specifications

Specifications apply at 23°C with KBr Window and Nitrogen encapsulating gas.

Symbol	Parameter	Min.	Тур.	Max.	Unit	Comments ^[1]	
AA	Active Area size	1.2 × 1.2		mm	Hot junction size, per element.		
А	Element Area	1.44 80 2		mm ²			
	Number of Junctions				Per element.		
	Number of Channels				Per detector package.		
V _s	Output Voltage	133 161 189		μV	DC, H = 330µW/cm ² ^[2]		
SNR	Signal-to-Noise Ratio	3,067	4,197	5,225	√Hz	DC, SNR = V _s /V _n	
R	Responsivity	28.0	33.9	39.8	V/W	DC, R = V _s /HA [3]	
R	Resistance	80	90	115	kΩ	Detector element	
	Temperature Coefficient of R		-0.04		%/°C	Best linear fit, 0° to 85°C [4]	
	Temperature Coefficient of R		0.02		%/°C	Best fit, 0° to 85°C [4]	
V _n	Noise Voltage	36.2	38.4	43.4	nV/√Hz	$V_n^2 = 4kTR$	
NEP	Noise Equivalent Power	0.91	1.13	1.55	nW/√Hz	DC, NEP = V _n HA/V _s ^[3]	
D*	Detectivity	0.77	1.06	1.32	10 ⁸ cm√Hz/Ω	DC, $D^* = V_s / V_n H \sqrt{A}^{[3]}$	
Т	Time Constant		25		ms	Chopped, -3dB point [4]	
FOV	Field of View	8°/60° TO-5		Degrees	For FOV description, see Package Outline Drawings		
	Package Type				Standard package hole size: 0.060" × 0.060"		
М	Element Matching	25 3.30		%	$\mathcal{M} = V_A - V_B /V_B^{[3]}$		
	Element Separation			mm	Center to center		
T _a	Operating Temperature	-50		+125	°C		
	Reference Filter, Central Wave Length		3.920		μm	Element A	
	CO ² Filter, Central Wave Length		4.260		μm	Element B	

^{1.} General specifications: Flat spectral response from 100nm to > $100\mu m$. Linear signal output from 10^{-6} to $0.1 W/cm^2$. Maximum incident radiance $0.1 W/cm^2$, damage threshold $\geq .5 W/cm^2$.

^{2.} Test conditions: 500K Blackbody source; Detector active surface 10cm from 0.6513cm diameter Blackbody Aperture.

^{3.} A is detector area in mm^2 .

^{4.} Parameter is not 100% tested. 90% of all units meet these specifications.

2. Package Outline Drawings

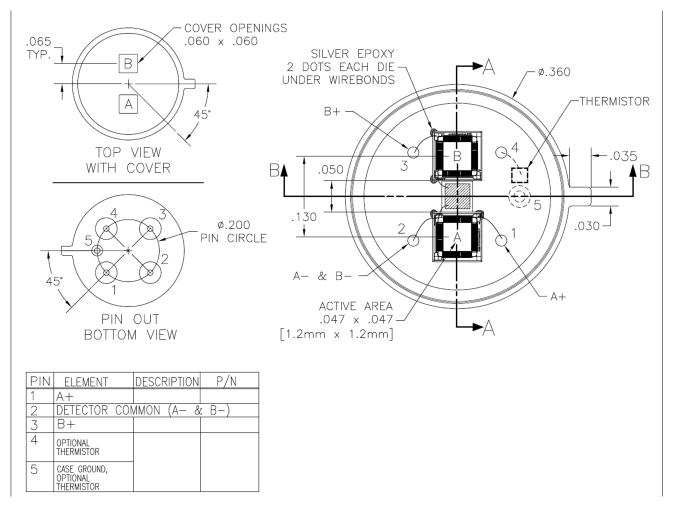


Figure 1. Package Outline Drawings - Top View

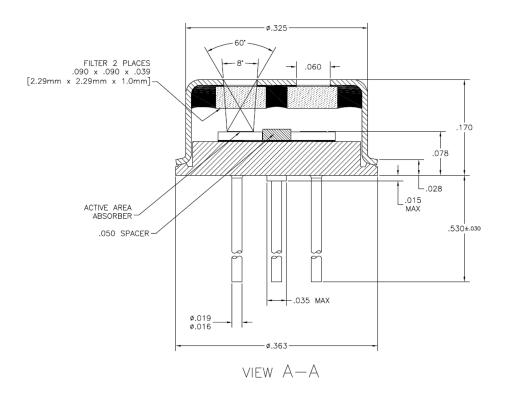


Figure 2. Package Outline Drawings - Side View

3. Ordering Information

Orderable Part Number	Package	Temperature	Carrier Type
RH5Z1222D20GZO#ADO	9.22mm TO-5 package	-50 to +125°C	Tray

4. Revision History

Revision	Date	Description
1.00	Aug 31, 2021	Initial release.

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